In the Claims:

(Previously Presented) A method of manufacturing a module, the method comprising:
providing a device that includes a connection area extending over a top surface of the
device, wherein the connection area comprises a compliant 3D structure that includes a
conductor overlying a compliant base element, the conductor being integral with a redistribution
layer that overlies the device;

applying a casting compound over the top surface of the device;

after applying a casting compound, reducing a thickness of the casting compound so that the connection area protrudes through the casting compound.

- 2. (Currently Amended) The method of claim 1 further comprising, after applying the casting compound, mounting the module to a [[the]] printed circuit board.
- 3. (Currently Amended) The method of claim 1 further comprising, after forming the casting compound, attaching the module to a [[the]] lead frame.
- 4. (Previously Presented) The method of claim 26 wherein electrically coupling the connection area comprises soldering the connection area to the terminal.
- 5. (Canceled)
- 6. (Canceled)
- 7. (Original) The method of claim 1 wherein the device comprises a semiconductor wafer.

- 8. (Original) The method of claim 7 and further comprising separating the wafer into a plurality of individual chips, wherein the casting compound is applied to the wafer before the separating.
- 9. (Original) The method of claim 8 wherein separation corridors between the chips on the wafer are exposed before the separating.
- 10. (Original) The method of claim 9 wherein the separation corridors are exposed by a photolithographic process.
- 11. (Original) The method of claim 9 wherein the separation corridors are exposed with use of a laser beam.
- 12. (Currently Amended) The method of claim 8 wherein the [[wafer]] casting compound is cooled to a temperature at which the casting compound is adequately brittle before separating the wafer into a plurality of individual chips.
- 13. (Original) The method of claim 1 wherein the casting compound is applied uniformly by spraying, dispensing or printing.
- 14. (Original) The method of claim 1 wherein the casting compound has thermal and mechanical properties comparable to those of silicon.
- 15. (Original) The method of claim 14 wherein the casting compound comprises a siliconbased material.

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- (Original) The method of claim 14 wherein the casting compound comprises a thermoplastic material.
- 17. (Original) The method of claim 14 wherein the casting compound comprises an epoxy resin.
- 18. (Canceled)
- 19. (Previously Presented) The method of claim 1 wherein the thickness of the casting compound is reduced by thermal removal.
- 20. (Previously Presented) The method of claim 1 wherein the thickness of the casting compound is reduced by etching.
- 21. (Previously Presented) A method for improving the mechanical properties of a BOC module arrangement in which chips have 3D structures which are mechanically and electrically connected by means of solder connections to terminal contacts on a printed circuit board or leadframe, the method characterized in that a casting compound is applied over a top surface of the chips, and excess thickness of the casting compound is removed, in such a way that tips of the 3D structures protrude from the compound, wherein the 3D structures comprise compliant 3D structures each of which includes a conductor overlying a compliant base element, the conductor being integral with a redistribution layer that overlies the top surface of the chips.
- 22. (Canceled)

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- 23. (Previously Presented) The method of claim 21 wherein the conductor comprises metal.
- 24. (Original) The method of claim 21 wherein the chips comprise a plurality of chips on a semiconductor wafer.
- 25. (Original) The method of claim 21 wherein the chips comprise individual semiconductor dies.
- 26. (Previously Presented) The method of claim 1, further comprising, after applying a casting compound, electrically coupling the connection area to a terminal of a second apparatus.
- 27. (Previously Presented) The method of claim 8, wherein separating the wafer into a plurality of individual chips comprises using a laser to separate the wafer.

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